

# Low Power Isolated Flyback Converter IC with Integrated Switching MOSFET

**BD7J101HFN-LB (Under Development) BD7J101EFJ-LB**

## General Description

This is the product guarantees long time support in Industrial market.

This IC is an optocoupler-less isolated flyback converter. It is not necessary to use any optocouplers and feedback circuits by a third winding of transformers; these have been ever required to obtain a stable output voltage in conventional applications. Furthermore, adoption of the original adapter type technology that controls on time makes the external phase compensation parts unnecessary, which realizes the designs of isolated power supply application with drastic reduction of parts number, minimization of application circuits, and high reliability.

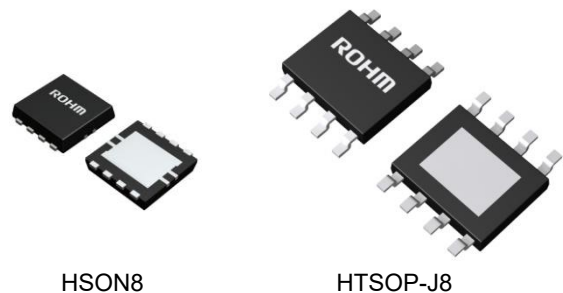
## Features

- Long Time Support Product for Industrial Applications
- No Need of Any Optocouplers and Third Winding of Transformers
- Set Output Voltage with Two External Resistors and Ratio of Transformer Turns
- Adopt of Original Adapter Type Technology that Controls On Time
- No Need of External Phase Compensation Parts by High-speed Load Response
- Low Output Ripple by Fixed Switching Frequency (At normal operation)
- High Efficient Light Load Mode (At PFM operation)
- Shutdown and Enable Control
- Built-in 120 V Switching MOSFET
- Soft Start Function
- Load Compensation Function
- Various Protection Function
  - Input Under Voltage Lockout (VIN UVLO)
  - Over Current Protection (OCP)
  - Over Voltage Protection (OVP)
  - Short Circuit Protection (SCP)
  - Thermal Shutdown (TSD)
  - Battery Short Protection (BSP)
  - Enable Over Voltage Protection (ENOVP)

## Key Specifications

- Power Supply Voltage Range
  - VIN Pin: 8 V to 80 V
  - SW Pin: 120 V (Max)
- Over Current Protection Current: 0.90 A (Typ)
- Switching Frequency: 400 kHz (Typ)
- Reference Voltage Accuracy: ±1.6 %
- Current at Shutdown: 0 μA (Typ)
- Current at Switching Operation: 0.45 mA (Typ)
- Operating Temperature Range: -40 °C to +125 °C

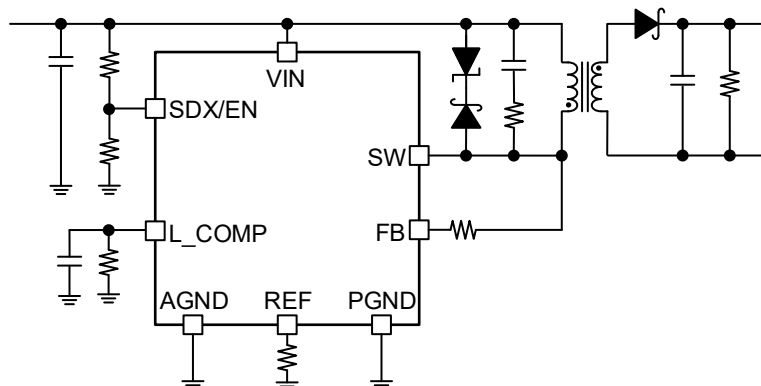
Packages	W (Typ) x D (Typ) x H (Max)
HSO8 (BD7J101HFN-LB (Under Development))	2.9 mm x 3.0 mm x 0.6 mm
HTSOP-J8 (BD7J101EFJ-LB)	4.9 mm x 6.0 mm x 1.0 mm



## Application

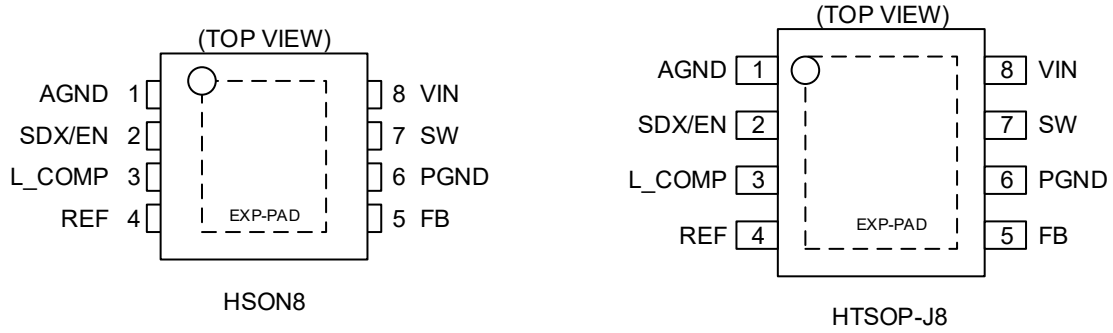
- Isolated Power Supply for Industrial Equipment

## Typical Application Circuit



○Product structure : Silicon integrated circuit ○This product has no designed protection against radioactive rays.

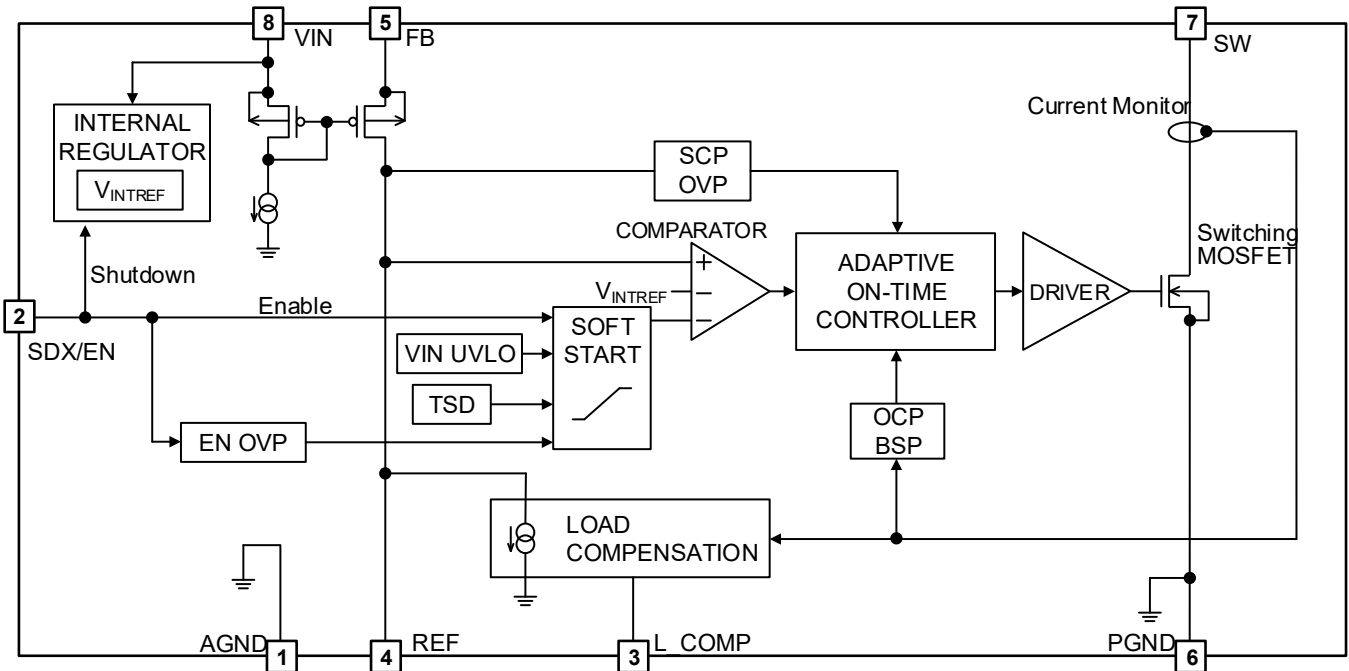
Pin Configurations



Pin Descriptions

Pin No.	Pin Name	Function
1	AGND	Analog system GND pin
2	SDX/EN	Shutdown and enable control pin
3	L_COMP	Setting pin of the load current compensation value
4	REF	Setting pin of the output voltage
5	FB	Setting pin of the output voltage
6	PGND	Power system GND pin
7	SW	Switching output pin
8	VIN	Power supply input pin
-	EXP-PAD	Connect EXP-PAD to both of the AGND and PGND pins

Block Diagram



Description of Blocks

1 INTERNAL REGULATOR

This is the regulator block for internal circuits.

This block also shuts itself down at the shutdown status of the SDX/EN pin voltage  $\leq V_{SDX}$ .

The SDX/EN pin voltage becomes  $V_{EN1}$  or more, the IC becomes enable status then it startup.

During  $t_{SS}$  from startup, the output voltage gradually rises due to the soft start function.

The SDX/EN pin voltage becomes  $V_{EN2}$  or less, the IC becomes disable status and stops the switching operation.

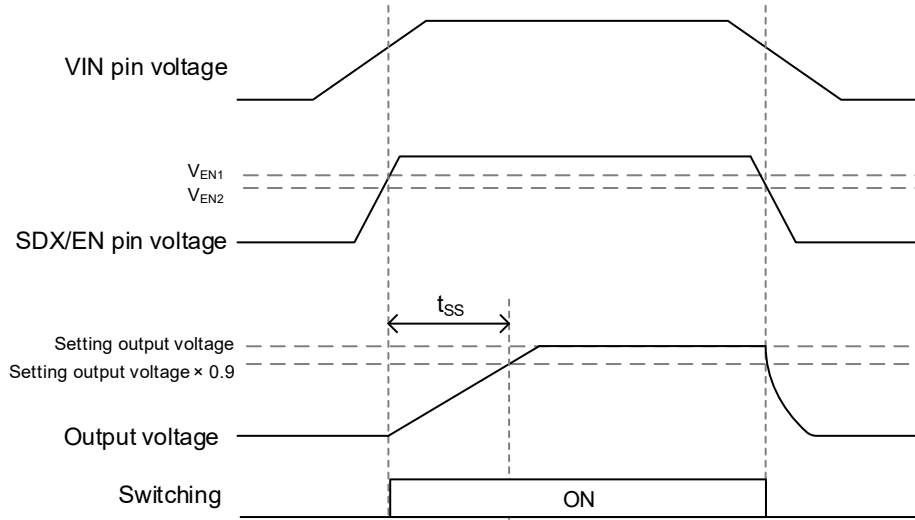


Figure 1. Startup and Stop Timing Chart

In the control method of this IC, it is necessary to operate in the status that the duty is  $D_{MAX}$  or less. At the startup and stop, set the VIN pin voltage  $V_{IN}$  to meet the next formula.

$$V_{IN} > \frac{N_P}{N_S} \times (V_{OUT} + V_F) \left( \frac{1}{D_{MAX}} - 1 \right) \quad [V]$$

where:

$V_{IN}$  is the VIN pin voltage.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{OUT}$  is the output voltage.

$V_F$  is the forward voltage of the secondary output diode.

$D_{MAX}$  is the maximum duty.

In the case that the SDX/EN pin is shorted to the VIN pin, the duty becomes  $D_{MAX}$  or more at startup and stop, and unintended output voltage may occur. Refer to [Application Examples: 6 Enable Voltage and Disable Voltage](#) for the enable control by the VIN pin.

## Description of Blocks – continued

**2 VIN UVLO**

This is the input low voltage protection block.

When the VIN pin voltage becomes  $V_{UVLO1}$  or less, the IC detects VIN UVLO and stops the switching operation.

When the VIN pin voltage becomes  $V_{UVLO2}$  or more, the IC releases VIN UVLO and starts the switching operation.

During  $t_{SS}$  from the start of switching operation, the output voltage gradually rises due to the soft start function.

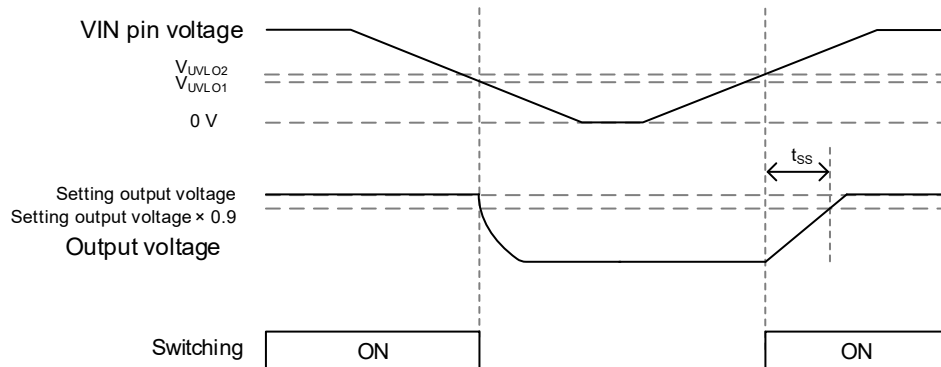


Figure 2. VIN UVLO Timing Chart

**3 EN OVP**

This is the SDX/EN pin voltage over voltage protection block.

When the SDX/EN pin voltage becomes  $V_{ENOV1}$  or more, the IC detects EN OVP and stops the switching operation.

When the SDX/EN pin voltage becomes  $V_{ENOV2}$  or less, the IC releases EN OVP and starts the switching operation.

During  $t_{SS}$  from the start of switching operation, the output voltage gradually rises due to the soft start function.

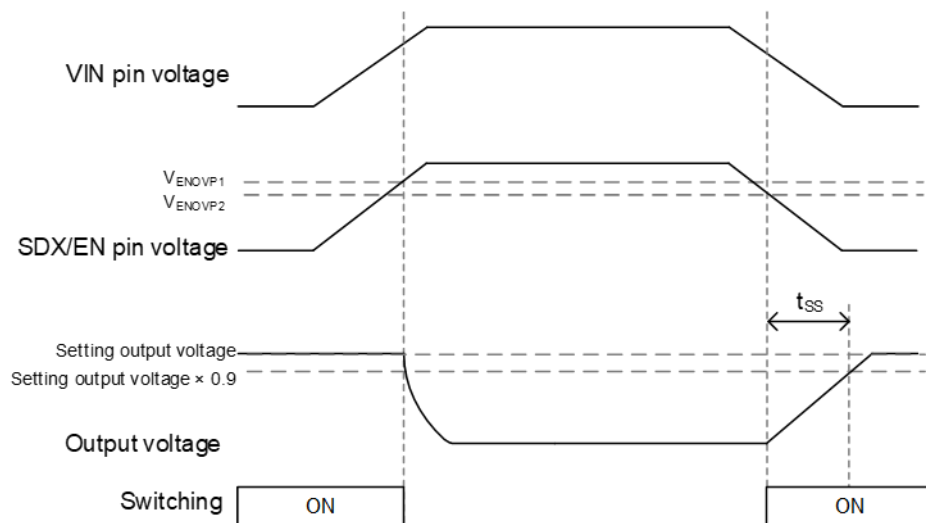


Figure 3. EN OVP Timing Chart

Refer [Application Examples:7 Enable OVP Detect Voltage and Enable OVP Release Voltage](#) for the enable control by the VIN pin.

**4 SOFT START**

When the SDX/EN pin voltage becomes  $V_{EN1}$  or more and enable status, the comparison voltage in the comparator block transits slowly 0 V to  $V_{INTREF}$ . This operation prevents the IC from rushing current at the rising edge of the output voltage or overshooting of the output voltage. The soft start time is fixed to  $t_{SS}$  in the IC.

**5 COMPARATOR**

In this block, the IC compares the reference voltage to the REF pin voltage that is the feedback voltage of the SW pin voltage. This IC is superior to the response for fluctuation in load because it constitutes the feedback loop by the comparator.

Description of Blocks – continued

6 ADAPTIVE ON TIME CONTROLLER

This block is corresponded to the original adapter type technology that controls on time.

- Stable load current: Operates in the PWM control and fix the on time.
- Fluctuating load current: Operates in the on time control and realizes a high-speed load response by fluctuates the switching frequency.
- Light load: Decrease the switching frequency and realizes a high efficiency.

When the load current fluctuates, the frequency becomes high. The IC raises the average of primary current by shortening the off time and raises the secondary current.

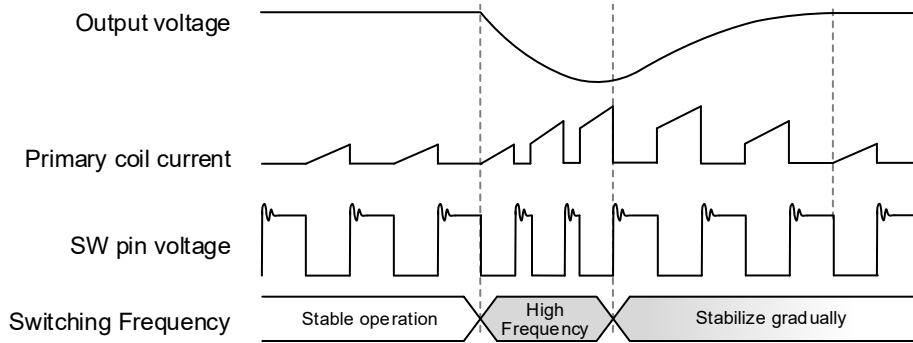


Figure 4. Transient Response Timing Chart

7 DRIVER

This block drives the switching MOSFET.

8 LOAD COMPENSATION

This block compensates the fluctuation of output voltage caused by the fluctuation of  $V_F$  characteristic in the secondary output diode corresponded to load current. This block monitors the current flowed to the switching MOSFET and pulls the current corresponded to the quantity of compensation determined by the external resistor and capacitor at the L\_COMP pin and time constant from the REF pin. The decrease of the REF pin voltage by the drop of feedback current flowing in the external resistor at the REF pin rises the output voltage and it is compensated.

Description of Blocks – continued

9 OCP, BSP

This is the block of the over current protection and battery short protection.

9.1 OCP (Over Current Protection)

At the switching MOSFET on, the IC detects OCP when the peak current becomes  $I_{LIMIT}$  or more. At this moment, the switching MOSFET is turned off. Because of detecting OCP per switching cycles and restricting on duty, the output voltage drops. In addition, to prevent detection error, the detection of OCP is invalidated for  $t_{MASK1}$  after the switching MOSFET is turned on.

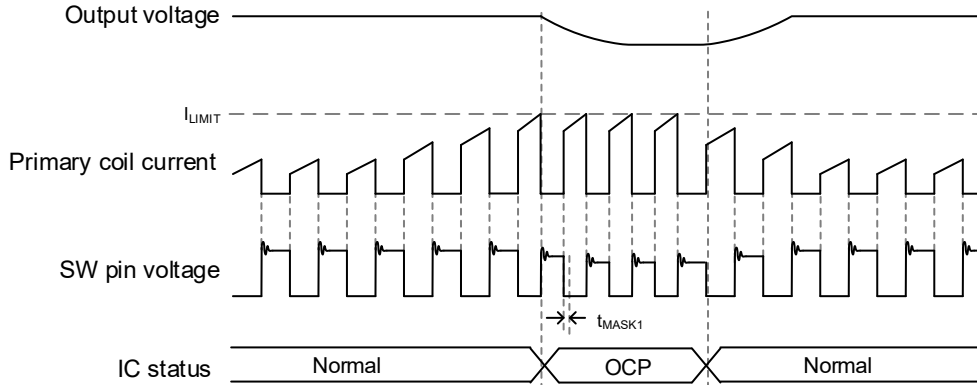


Figure 5. OCP Timing Chart

9.2 BSP (Battery Short Protection)

If the SW pin is connected to high electric potential with low impedance, large current flows when the switching MOSFET turned on and it may destroy the IC. To prevent this, BSP is built in the IC. When the SW pin voltage becomes  $V_{BSP}$  or more at the switching MOSFET on, the IC detects BSP and the switching operation is stopped. The time of  $t_{RESTART}$  after the switching operation stopped, the switching operation is restarted. During  $t_{SS}$  from the start of switching operation, the output voltage gradually rises due to the soft start function.

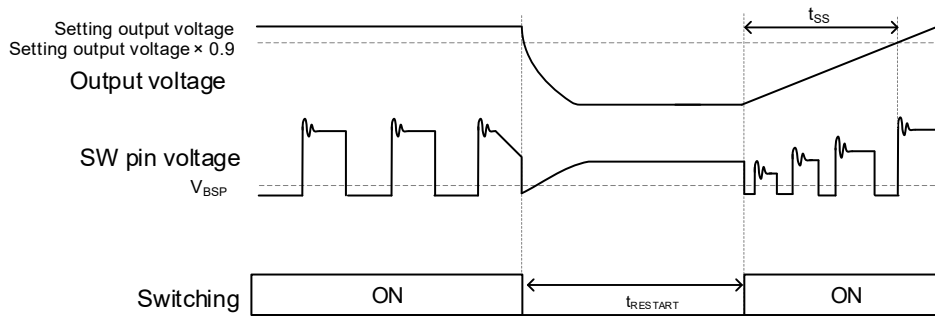


Figure 6. BSP Timing Chart

Description of Blocks – continued

10 SCP, OVP

This is the block of the short circuit protection and over voltage protection.

10.1 SCP (Short Circuit Protection)

The REF pin obtains the secondary output voltage data from the primary flyback voltage. When the REF pin voltage becomes  $V_{SCP}$  or less at the switching MOSFET off, the IC detects SCP and the switching operation is stopped. The time of  $t_{RESTART}$  after the switching operation stopped, the switching operation is restarted. The soft start function works and the output from restart of the switching operation to the time of  $t_{SS}$ , and the output voltage rises slowly.

To prevent detection error, the detection of SCP is invalidated for  $t_{MASK2}$  after the switching MOSFET is turned off and for  $t_{MASK3}$  from start of the switching operation.

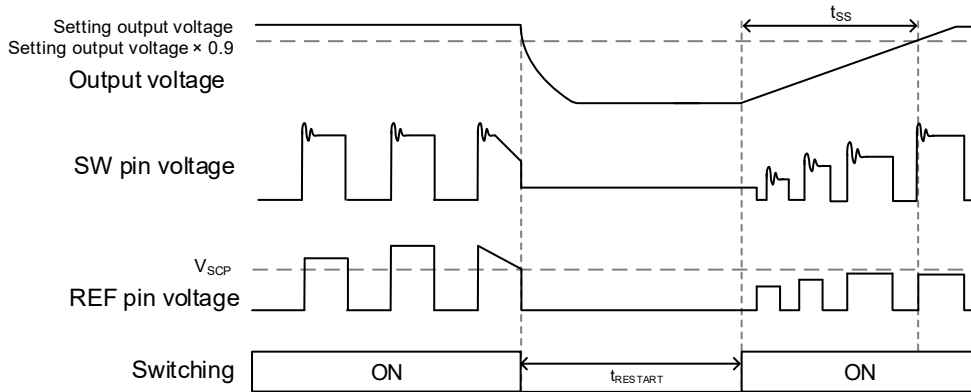


Figure 7. SCP Timing Chart

10.2 OVP (Over Voltage Protection)

The REF pin obtains the secondary output voltage data from the primary flyback voltage. When the REF pin voltage becomes  $V_{OVP}$  or more at the switching MOSFET off, the IC detects OVP and the switching operation is stopped. The time of  $t_{RESTART}$  after the switching operation stopped, the switching operation is restarted. The soft start function works and the output from restart of the switching operation to the time of  $t_{SS}$ , and the output voltage rises slowly.

To prevent detection error, the detection of OVP is invalidated for  $t_{MASK2}$  after the switching MOSFET is turned off.

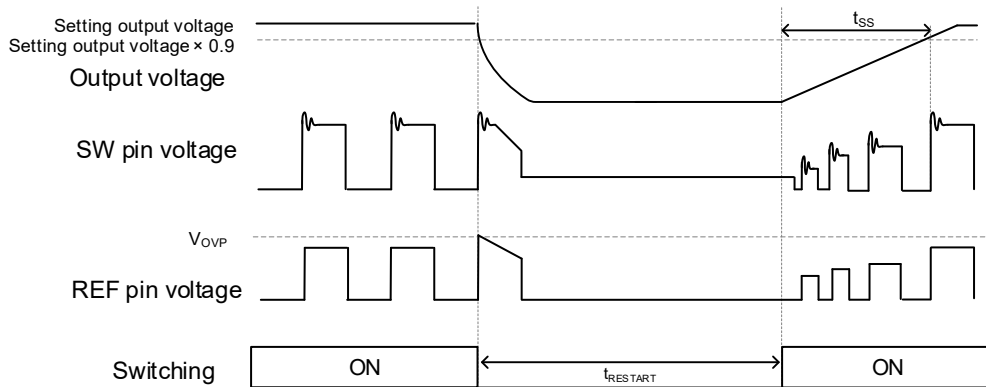


Figure 8. OVP Timing Chart

## Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Rating	Unit
VIN Pin Voltage	V <sub>IN_MAX</sub>	100	V
SW Pin Voltage	V <sub>SW_MAX</sub>	120	V
SDX/EN Pin Voltage	V <sub>SDX/EN_MAX</sub>	100	V
FB Pin Voltage	V <sub>FB_MAX</sub>	V <sub>IN</sub> -0.3 to V <sub>IN</sub> +0.3	V
REF Pin Voltage	V <sub>REF_MAX</sub>	7	V
L_COMP Pin Voltage	V <sub>L_COMP_MAX</sub>	7	V
Maximum Junction Temperature	T <sub>jmax</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

**Caution 1:** Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

**Caution 2:** Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

## Thermal Resistance (Note 1)

Parameter	Symbol	Thermal Resistance (Typ)		Unit
		1s <sup>(Note 3)</sup>	2s2p <sup>(Note 4)</sup>	
HSO8				
Junction to Ambient	θ <sub>JA</sub>	265.1	66.1	°C/W
Junction to Top Characterization Parameter <sup>(Note 2)</sup>	Ψ <sub>JT</sub>	17	9	°C/W
HTSOP-J8				
Junction to Ambient	θ <sub>JA</sub>	206.4	45.2	°C/W
Junction to Top Characterization Parameter <sup>(Note 2)</sup>	Ψ <sub>JT</sub>	21	13	°C/W

(Note 1) Based on JE5D51-2A (Still-Air).

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 3) Using a PCB board based on JE5D51-3.

(Note 4) Using a PCB board based on JE5D51-5, 7.

Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3 mm x 76.2 mm x 1.57 mmt

Top	
Copper Pattern	Thickness
Footprints and Traces	70 μm

Layer Number of Measurement Board	Material	Board Size	Thermal Via <sup>(Note 5)</sup>	
			Pitch	Diameter
4 Layers	FR-4	114.3 mm x 76.2 mm x 1.6 mmt	1.20 mm	Φ0.30 mm

Top		2 Internal Layers		Bottom	
Copper Pattern	Thickness	Copper Pattern	Thickness	Copper Pattern	Thickness
Footprints and Traces	70 μm	74.2 mm x 74.2 mm	35 μm	74.2 mm x 74.2 mm	70 μm

(Note 5) This thermal via connects with the copper pattern of all layers.

## Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Power Supply Voltage Range 1	V <sub>IN</sub>	8	48	80	V	The VIN pin voltage
Power Supply Voltage Range 2	V <sub>SW</sub>	-	-	110	V	The SW pin Voltage
Power Supply Voltage Range 3	V <sub>L_COMP_MAX2</sub>	-	-	0.5	V	The L_COMP pin voltage
Operating Temperature	T <sub>opr</sub>	-40	-	+125	°C	



Electrical Characteristics (Unless otherwise specified  $V_{IN} = 48\text{ V}$ ,  $V_{SDX/EN} = 2.5\text{ V}$ ,  $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
<b>Power Supply Block</b>						
Current at Shutdown	$I_{ST}$	-	0	10	$\mu\text{A}$	$V_{SDX/EN} = 0\text{ V}$
Current at Switching Operation	$I_{CC}$	-	0.45	1.10	mA	$V_{REF} = 0.85\text{ V}$ (At PFM operation)
VIN UVLO Voltage 1	$V_{UVLO1}$	4.0	5.0	6.0	V	At $V_{IN}$ falling
VIN UVLO Voltage 2	$V_{UVLO2}$	4.2	5.2	6.2	V	At $V_{IN}$ rising
VIN UVLO Voltage Hysteresis	$V_{UVLO\_HYS}$	-	0.2	-	V	
<b>Shutdown and Enable Control Block</b>						
Shutdown Voltage	$V_{SDX}$	-	-	0.3	V	
Enable Voltage 1	$V_{EN1}$	1.75	2.00	2.25	V	At $V_{SDX/EN}$ rising
Enable Voltage 2	$V_{EN2}$	1.55	1.80	2.05	V	At $V_{SDX/EN}$ falling
Enable Voltage Hysteresis	$V_{EN\_HYS}$	-	0.2	-	V	
Enable Over Protection Voltage 1	$V_{ENOV1}$	3.06	3.50	3.94	V	At $V_{SDX/EN}$ rising
Enable Over Protection Voltage 2	$V_{ENOV2}$	2.86	3.30	3.74	V	At $V_{SDX/EN}$ falling
Enable Over Protection Voltage Hysteresis	$V_{ENOV\_HYS}$	-	0.2	-	V	
SDX/EN Pin Inflow Current	$I_{SDX/EN}$	0.89	1.78	2.85	$\mu\text{A}$	
SDX/EN Pin Clamp Voltage	$V_{CLPEN}$	-	5.3	-	V	
SDX/EN Pin Pull-down Resistance 1	$R_{SDX/EN1}$	-	1315	-	$\text{k}\Omega$	
SDX/EN Pin Pull-down Resistance 2	$R_{SDX/EN2}$	-	106	-	$\text{k}\Omega$	
SDX/EN Pin Pull-down Resistance 3	$R_{SDX/EN3}$	-	1421	-	$\text{k}\Omega$	
SDX/EN Pin Pull-down Resistance 4	$R_{SDX/EN4}$	-	33	-	$\text{k}\Omega$	
<b>Reference Voltage Block</b>						
Reference Voltage	$V_{INTREF}$	0.738	0.750	0.762	V	
REF Pin Current	$I_{REF}$	-	100	-	$\mu\text{A}$	
<b>Switching Block</b>						
On Resistance	$R_{ON}$	0.25	0.50	1.00	$\Omega$	Between SW and PGND pins
Over Current Protection Current	$I_{LIMIT}$	0.72	0.90	1.08	A	
Switching Frequency	$f_{SW}$	-	400	-	kHz	At PWM operation (Duty=30 %)
On Time	$t_{ON}$	0.60	0.75	0.90	$\mu\text{s}$	At PWM operation (Duty=30 %)
Minimum On Time	$t_{ON\_MIN}$	280	380	480	ns	
Minimum Off Time	$t_{OFF\_MIN}$	410	550	690	ns	
Maximum Off Time	$t_{OFF\_MAX}$	14	20	26	$\mu\text{s}$	
Soft Start Time	$t_{SS}$	0.8	2.0	4.5	ms	From rise-up to $V_{REF} \times 90\%$
Maximum Duty	$D_{MAX}$	50	-	-	%	
Minimum Duty	$D_{MIN}$	-	-	20	%	
<b>Protection Function Block</b>						
Short Circuit Protection Detection Voltage	$V_{SCP}$	-	0.50	-	V	
Over Voltage Protection Detection Voltage	$V_{OVP}$	-	0.95	-	V	
Battery Short Protection Detection Voltage	$V_{BSP}$	-	2.0	-	V	
Restart Time	$t_{RESTART}$	-	2.0	-	ms	
Over Current Protection Mask Time	$t_{MASK1}$	-	280	-	ns	
Short and Over Voltage Protection Mask Time	$t_{MASK2}$	-	430	-	ns	
Short Protection Mask Time at Startup	$t_{MASK3}$	-	550	-	$\mu\text{s}$	
<b>Load Compensation Block</b>						
Internal Resistor at L_COMP Pin	$R_{INTCOMP}$	-	100	-	$\text{k}\Omega$	
Compressor Magnification in Current Monitor	K	-	0.005	-	%	

Typical Performance Curves

(Reference Data)

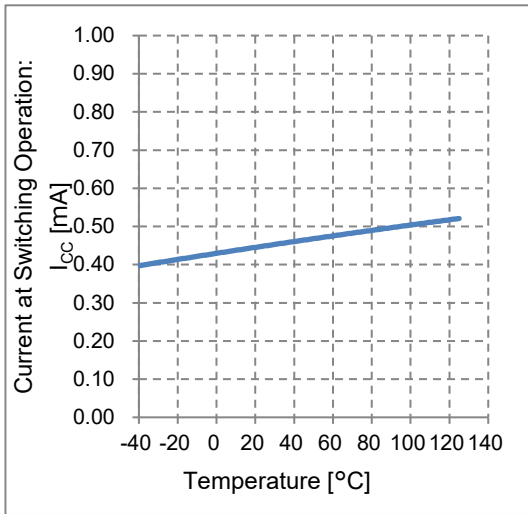


Figure 9. Current at Switching Operation vs Temperature

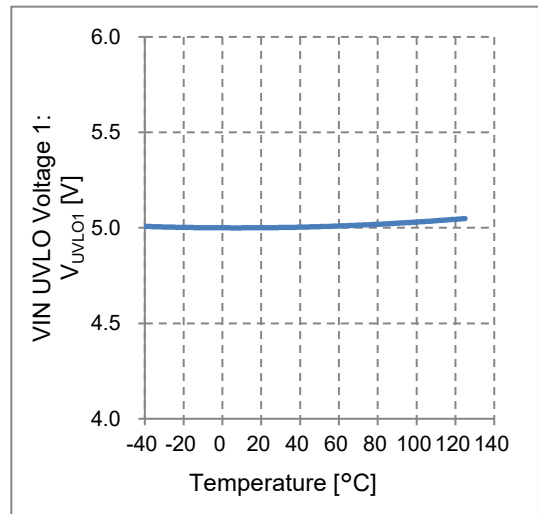


Figure 10. VIN UVLO Voltage 1 vs Temperature

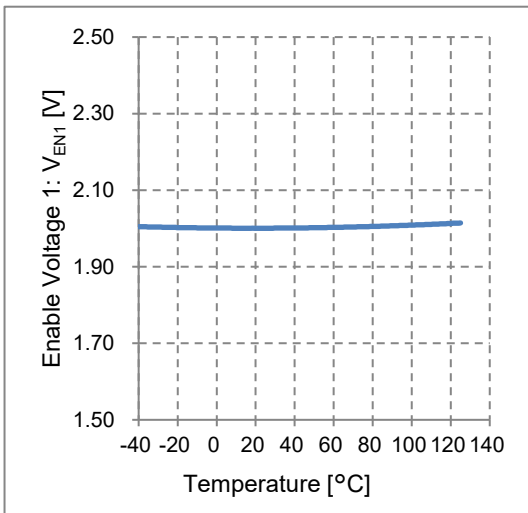


Figure 11. Enable Voltage 1 vs Temperature

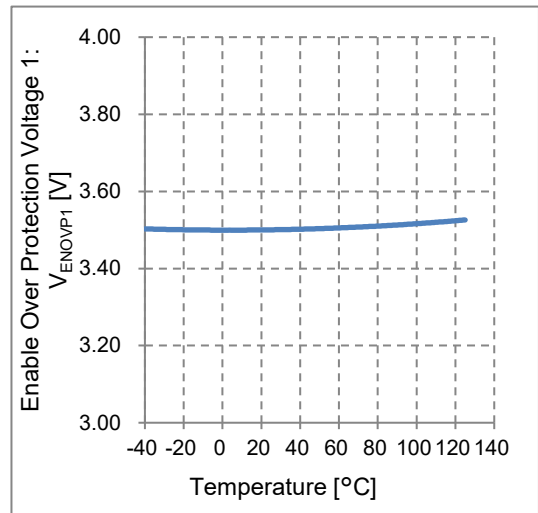


Figure 12. Enable Over Protection Voltage 1 vs Temperature

Typical Performance Curves – continued

(Reference Data)

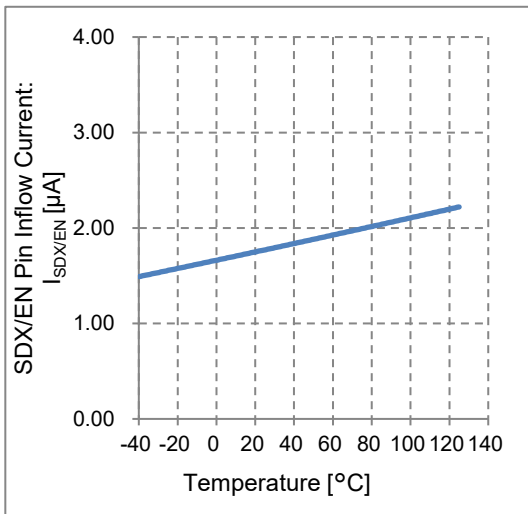


Figure 13. SDX/EN Pin Inflow Current vs Temperature

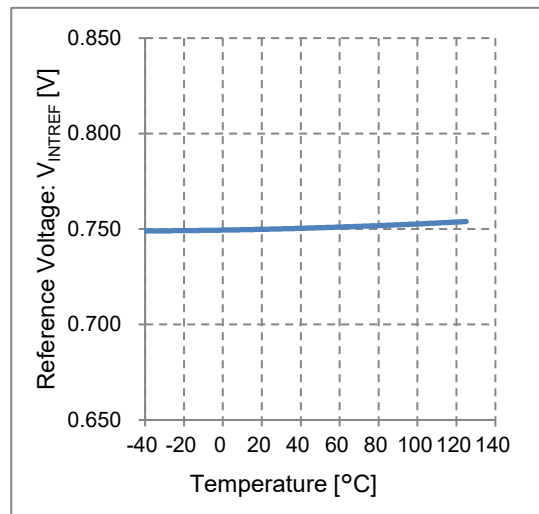


Figure 14. Reference Voltage vs Temperature

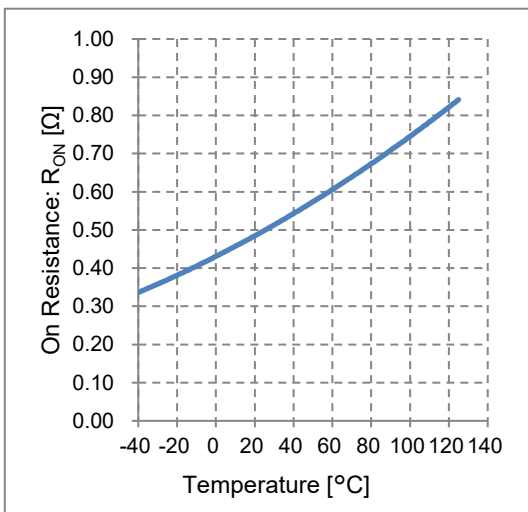


Figure 15. On Resistance vs Temperature

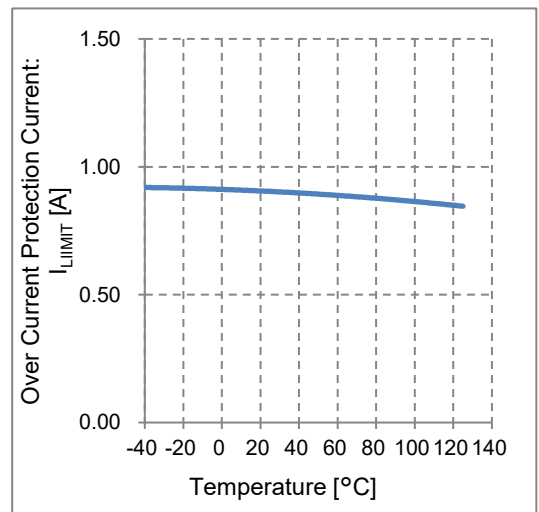


Figure 16. Over Current Protection Current vs Temperature

Typical Performance Curves – continued

(Reference Data)

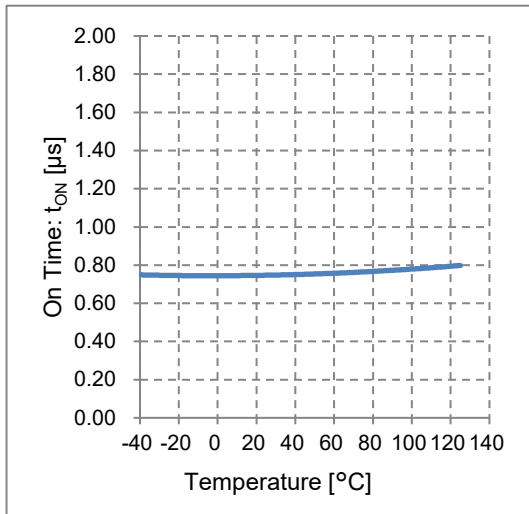


Figure 17. On Time vs Temperature

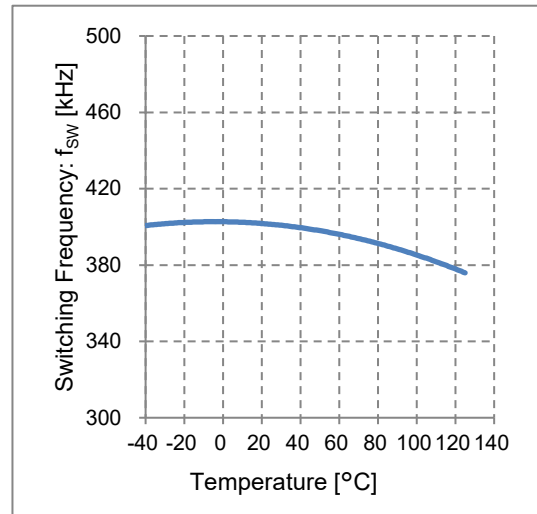


Figure 18. Switching Frequency vs Temperature

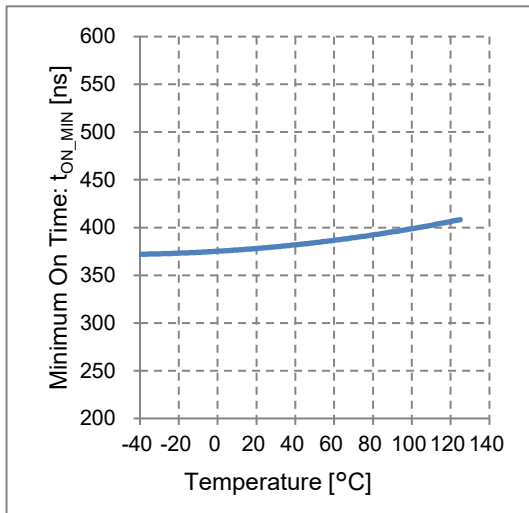


Figure 19. Minimum On Time vs Temperature

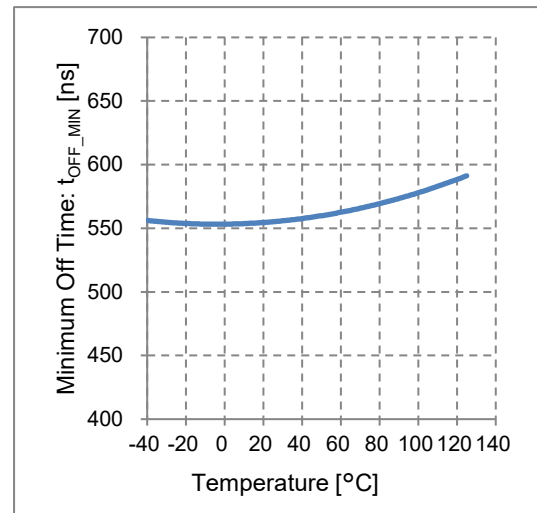


Figure 20. Minimum Off Time vs Temperature

Typical Performance Curves – continued

(Reference Data)

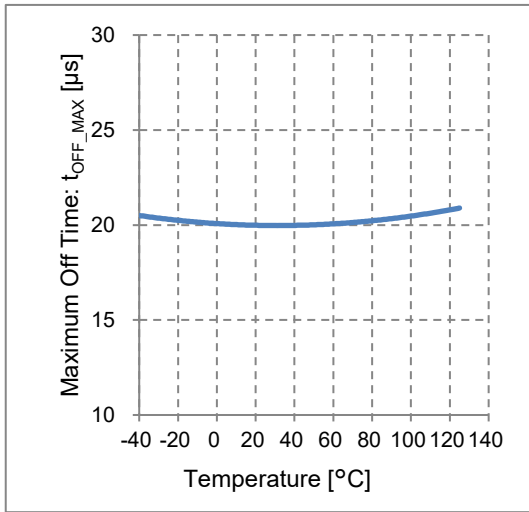


Figure 21. Maximum Off Time vs Temperature

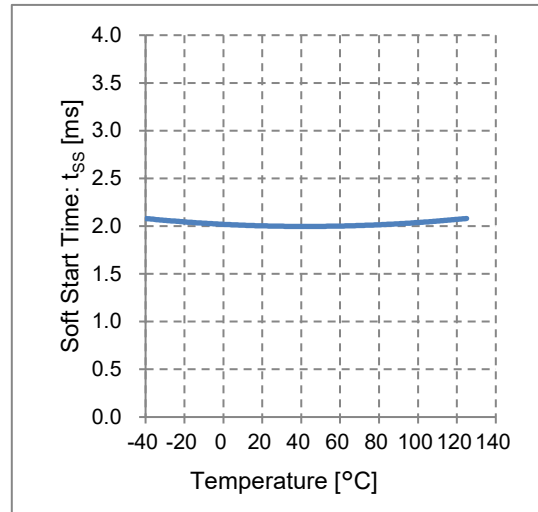


Figure 22. Soft Start Time vs Temperature

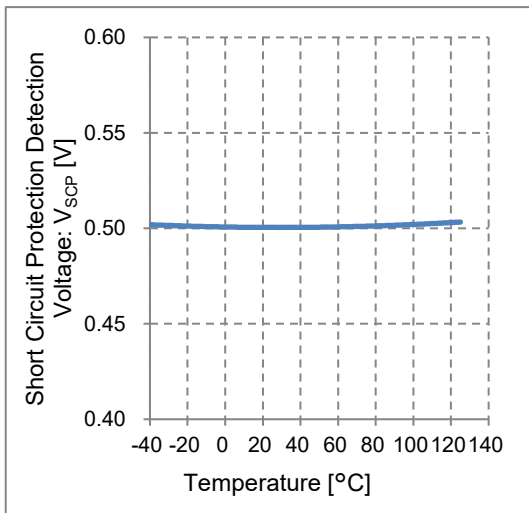


Figure 23. Short Circuit Protection Detection Voltage vs Temperature

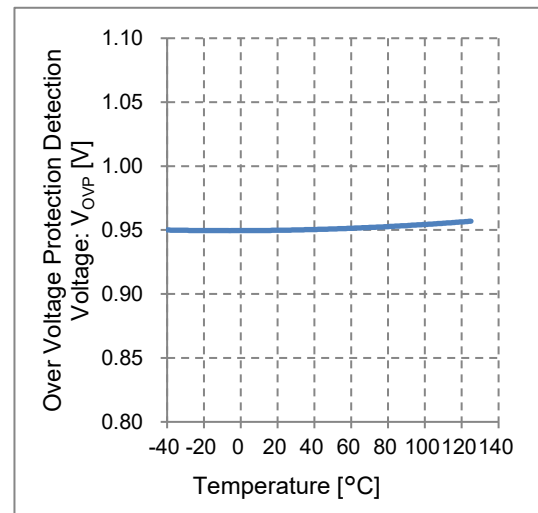


Figure 24. Over Voltage Protection Detection Voltage vs Temperature

Typical Performance Curves – continued

(Reference Data)

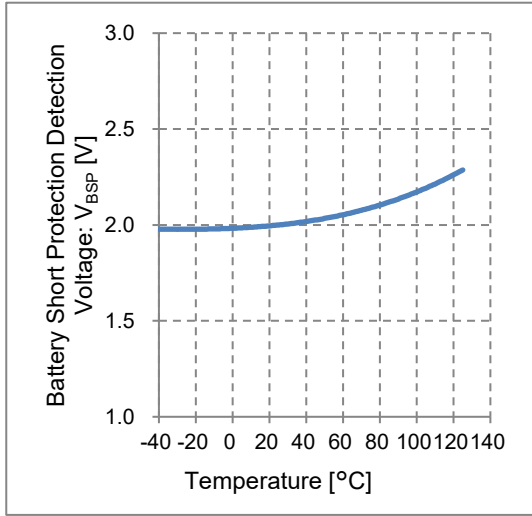


Figure 25. Battery Short Protection Detection Voltage vs Temperature

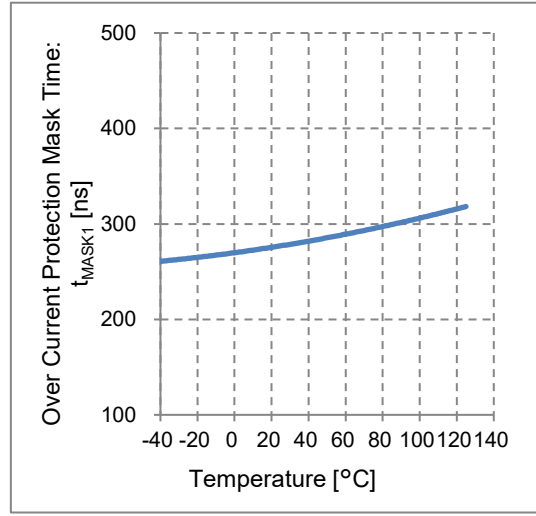


Figure 26. Over Current Protection Mask Time vs Temperature

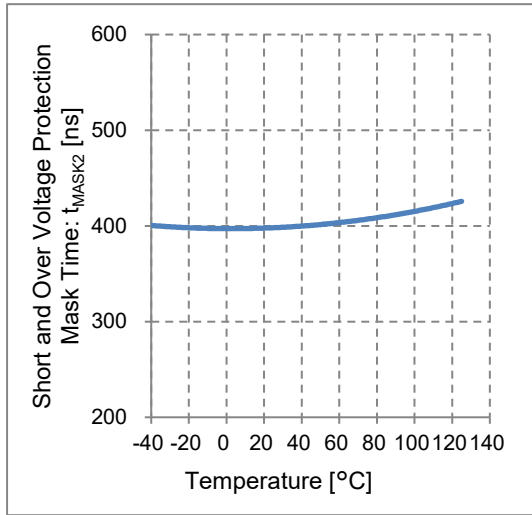


Figure 27. Short and Over Voltage Protection Mask Time vs Temperature

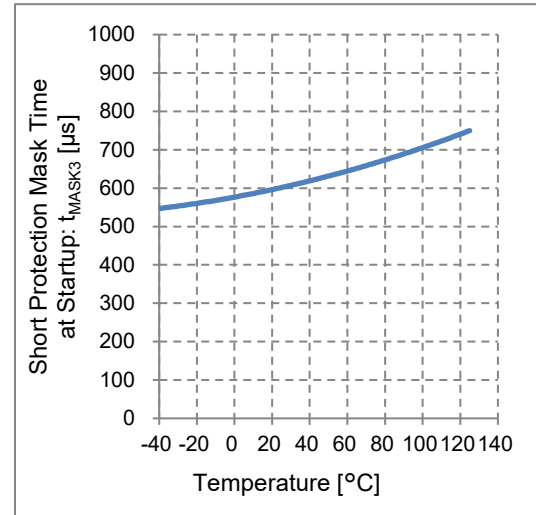


Figure 28. Short Protection Mask Time at Startup vs Temperature

Typical Performance Curves – continued

(Reference Data)

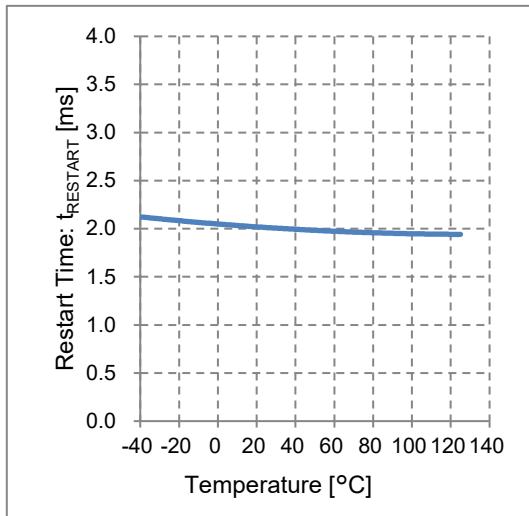


Figure 29. Restart Time vs Temperature

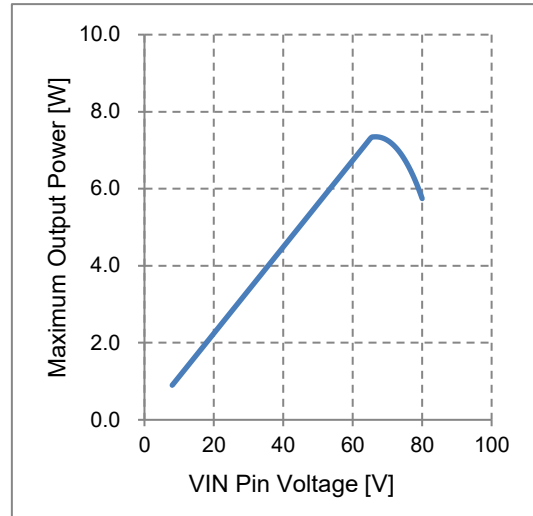


Figure 30. Maximum Output Power vs VIN Pin Voltage

## Application Examples

### 1 Output Voltage

When the internal switching MOSFET is off, the SW pin voltage becomes higher than the VIN pin voltage. The secondary output voltage is calculated by the primary flyback voltage, which is described by the difference between this SW pin voltage and VIN pin voltage. The SW pin voltage at turn off is calculated by the formula below.

$$V_{SW} = V_{IN} + \frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR) \quad [V]$$

where:

$V_{SW}$  is the SW pin voltage.

$V_{IN}$  is the VIN pin voltage.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{OUT}$  is the output voltage.

$V_F$  is the forward voltage of the secondary output diode.

$I_S$  is the secondary transformer current.

$ESR$  is the secondary total impedance (secondary transformer winding resistance and board).

The external resistor  $R_{FB}$  between the FB and SW pins converts the primary flyback voltage into the FB pin inflow current  $I_{RFB}$ . The FB pin inflow current  $I_{RFB}$  is calculated by the formula below because the FB pin voltage is nearly equal to the VIN pin voltage by the IC's internal circuit.

$$\begin{aligned} I_{RFB} &= \frac{V_{SW} - V_{FB}}{R_{FB}} \\ &= \frac{V_{IN} + \frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR) - V_{FB}}{R_{FB}} \\ &= \frac{\frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR)}{R_{FB}} \quad [A] \end{aligned}$$

where:

$I_{RFB}$  is the FB pin inflow current.

$V_{FB}$  is the FB pin voltage.

$R_{FB}$  is the external resistor between the FB and SW pins.

Furthermore, the REF pin voltage is calculated by the formula below because the FB pin inflow current flows into the external resistor  $R_{REF}$  between the REF and AGND pins.

$$V_{REF} = \frac{R_{REF}}{R_{FB}} \times \frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR) \quad [V]$$

where:

$V_{REF}$  is the REF pin voltage.

$R_{REF}$  is the external resistor between the REF and AGND pins.

It is necessary to be set the resistor  $R_{REF}$  as the current flowing in the REF pin becomes  $I_{REF}$  when the REF pin voltage is equal to  $V_{INTREF}$ . This IC's internal circuit is designed as  $R_{REF} = 7.5 \text{ k}\Omega$  according to the formula below.

$$R_{REF} = \frac{V_{INTREF}}{I_{REF}} \quad [\Omega]$$



1 Output Voltage – continued

The REF pin voltage is input to the comparator with the reference voltage in the IC. By the internal circuit in the IC, the REF pin voltage becomes equal to the reference voltage. Therefore, the output voltage and the REF pin voltage is calculated by the formula below.

$$V_{OUT} = \frac{R_{FB}}{R_{REF}} \times \frac{N_S}{N_P} \times V_{REF} - V_F - I_S \times ESR \quad [V]$$

The output voltage is set by the number of winding ratio of the primary and secondary transformer and the resistance ratio of  $R_{FB}$  and  $R_{REF}$ . In addition,  $V_F$  and  $ESR$  is factor of the error in the output voltage. According to the above formula, the external resistor between the FB and SW pins  $R_{FB}$  is calculated by the formula below.

$$R_{FB} = \frac{R_{REF}}{V_{REF}} \times \frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR) \quad [\Omega]$$

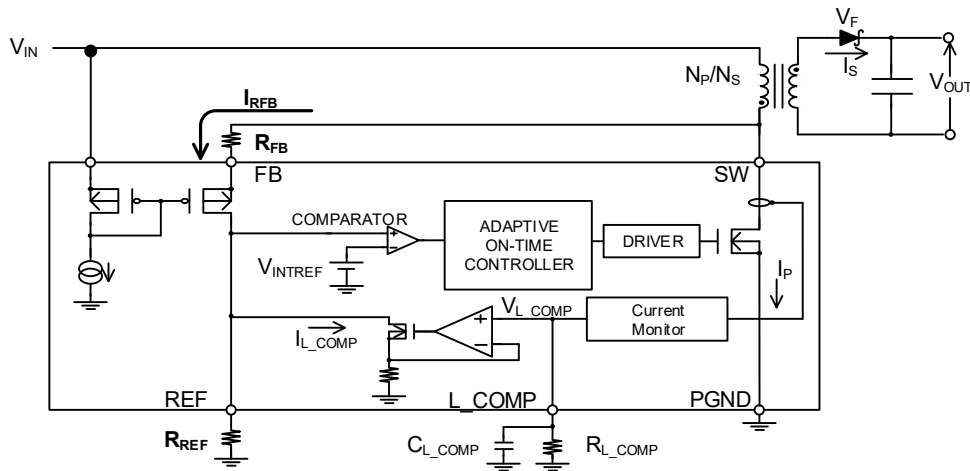


Figure 31. Control Block Diagram

## Application Examples – continued

## 2 Transformer

## 2.1 Number of Winding Ratio

The number of winding ratio is the parameter with which the output voltage, maximum output electric power, duty and the SW pin voltage is set.

The duty of flyback converter is calculated by the formula below.

$$Duty = \frac{\frac{N_P}{N_S} \times (V_{OUT} + V_F)}{V_{IN} + \frac{N_P}{N_S} \times (V_{OUT} + V_F)} \quad [\%]$$

where:

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{OUT}$  is the output voltage.

$V_F$  is the forward voltage of the secondary output diode.

$V_{IN}$  is the VIN pin voltage.

It is necessary to set the duty to  $D_{MAX}$  or less for the stable control. By the restriction of the minimum on time, the minimum duty is determined to  $D_{MIN}$  and the number of winding ratio must meet the conditional expression below.

$$\frac{D_{MIN}}{1 - D_{MIN}} \times \frac{V_{IN}}{V_{OUT} + V_F} < \frac{N_P}{N_S} < \frac{D_{MAX}}{1 - D_{MAX}} \times \frac{V_{IN}}{V_{OUT} + V_F}$$

where:

$D_{MIN}$  is the minimum duty.

$D_{MAX}$  is the maximum duty.

## 2 Transformer – continued

### 2.2 Primary Inductance

The right half plane zero point occurs in the feedback loop of flyback converter. The right half plane zero frequency  $f_{RHP\_ZERO}$  is calculated by the formula below.

$$f_{RHP\_ZERO} = \frac{\left(\frac{N_P}{N_S}\right)^2 \times \left\{ \frac{V_{IN}}{V_{IN} + \frac{N_P}{N_S} \times (V_{OUT} + V_F)} \right\}^2 \times R_{OUT}}{2\pi \times \frac{\frac{N_P}{N_S} \times (V_{OUT} + V_F)}{V_{IN} + \frac{N_P}{N_S} \times (V_{OUT} + V_F)} \times L_P} \quad [\text{Hz}]$$

where:

$f_{RHP\_ZERO}$  is the right half plane zero frequency.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{IN}$  is the VIN pin voltage.

$V_{OUT}$  is the output voltage.

$V_F$  is the forward voltage of the secondary output diode.

$R_{OUT}$  is the load resistance.

$L_p$  is the primary inductance.

For the insurance of stability, the right half plane zero frequency  $f_{RHP\_ZERO}$  must be set to more than one quarter of the switching frequency  $f_{SW}$ . By this, the conditional expression below is required.

$$f_{RHP\_ZERO} > \frac{1}{4} \times f_{SW}$$

$$L_p < \frac{2 \times \text{Duty} \times V_{IN}^2}{(V_{OUT} + V_F) \times I_{OUT\_MAX} \times \pi \times f_{SW}} \quad [\text{H}]$$

where:

$f_{SW}$  is the switching frequency.

$I_{OUT\_MAX}$  is the maximum value of the output current.

## 2.2 Primary Inductance – continued

The minimum value of primary inductance can be found by the relation of input and output electric power. If the  $L_p$  becomes lower, the peak current of primary transformer becomes higher. Because the desired output electric power cannot be obtained if the peak current value becomes the over current protection current or more, the lower limit of the necessary primary inductance value corresponding to maximum load is calculated by the conditional expression below.

$$L_p > \frac{1}{2} \times \frac{V_{IN}^2 \times t_s \times Duty^2 \times \eta}{I_{LIMIT\_MIN} \times Duty \times V_{IN} \times \eta - V_{OUT\_MAX} \times I_{OUT\_MAX}} \quad [H]$$

where:

$t_s$  is the cycle of switching.

$\eta$  is the efficiency.

$I_{LIMIT\_MIN}$  is the minimum value of over current protection current.

$V_{OUT\_MAX}$  is the maximum value of output voltage.

According to the above, the primary inductance must meet the conditional expression below.

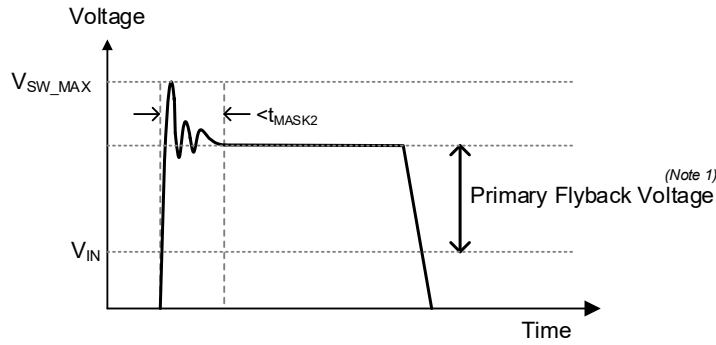
$$\frac{1}{2} \times \frac{V_{IN}^2 \times t_s \times Duty^2 \times \eta}{I_{LIMIT\_MIN} \times Duty \times V_{IN} \times \eta - V_{OUT\_MAX} \times I_{OUT\_MAX}}$$

$$< L_p < \frac{2 \times Duty \times V_{IN}^2}{(V_{OUT} + V_F) \times I_{OUT\_MAX} \times \pi \times f_{SW}} \quad [H]$$

2 Transformer – continued

2.3 Leak Inductance

The moment the internal switching MOSFET is turned off, the leak inductance of transformer causes the ringing at the SW pin. Insert the snubber circuit not to exceed the absolute maximum rating of the SW pin voltage. It is necessary to settle down within  $t_{MASK2}$  for the prevention of the error in the secondary output voltage.



(Note 1) Primary Flyback Voltage =  $\frac{N_P}{N_S} \times (V_{OUT} + V_F + I_S \times ESR)$

Figure 32. Leak Inductance

2.4 Winding Resistance

The primary winding resistance lowers the efficiency of electricity. The secondary winding resistance also lowers the output voltage as well as the efficiency of electricity. According to them, it is recommended to use the transformer which has small winding resistance.

2.5 Saturated Current

Because the core of transformer saturates if the primary transformer current exceeds its rating saturated current, the energy does not transmit to the secondary side. The primary transformer current increases rapidly because the inductance value drops if the core saturates. Set the primary transformer current to less than its rating saturated current.

3 Output Capacitor

It is necessary to select the proper secondary output capacitor for the stable operation. Refer to the formula below and select the appropriate capacitor.

$$C_{OUT} = 1.6 \times 10^{-9} \times \frac{1}{L_P} \times \left( \frac{N_P}{N_S} \times Duty \right)^2 \quad [F]$$

where:

$C_{OUT}$  is the value of output capacitor.

$L_P$  is the primary inductance.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

In addition, it is necessary for the output voltage to rise within  $t_{SS}$ . Therefore, consider the conditional expression below to select the output capacitor too. The startup error may occur because the short circuit protection operates if the capacitor value is extremely large.

$$C_{OUT} \leq \frac{1}{2} \times \frac{t_{SS} \times \left\{ \left( I_{LIMIT\_MIN} \times \frac{N_P}{N_S} \right) \times (1 - Duty) - I_{OUT\_MAX} \right\}}{V_{OUT}} \quad [F]$$

where:

$t_{SS}$  is the soft start time.

$I_{LIMIT\_MIN}$  is the minimum value of over current protection current.

$I_{OUT\_MAX}$  is the maximum value of output current.

$V_{OUT}$  is the output voltage.

**Application Examples – continued****4 Input Capacitor**

Use the ceramic capacitor for the input capacitor and locate the input capacitor as near as possible to the VIN pin. The pattern of board and location of capacitor may cause malfunction. It is necessary to set the value of input capacitor so that the ripple voltage of the VIN pin becomes 4 % or less of the VIN pin voltage. Confirm that at the load fluctuation and startup too.

**5 Secondary Output Diode**

It is recommended to use the schottky barrier diode whose forward voltage  $V_F$  is small because the  $V_F$  becomes the factor of error in the output voltage. Select the secondary output diode so that the forward current does not exceed its rating. The reverse voltage  $V_R$  occurring at the secondary output diode is calculated by the formula below when the internal switching MOSFET is on.

$$V_R = V_{IN} \times \frac{N_S}{N_P} + V_{OUT} \quad [V]$$

where:

$V_R$  is the reverse voltage at the secondary output diode.

$V_{IN}$  is the VIN pin voltage.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{OUT}$  is the output voltage.

Furthermore, the ringing piles up the reverse voltage  $V_R$  at the secondary output diode the moment the internal switching MOSFET is turned on. Set the peak voltage of  $V_R$  not to exceed the rating of secondary output diode.

Application Examples – continued

6 Enable Voltage and Disable Voltage

This IC becomes shutdown status when the SDX/EN pin voltage becomes  $V_{SDX}$  or less. At the rise of the SDX/EN pin voltage, the IC becomes enable status and starts the operation when the voltage becomes  $V_{EN1}$  or more. At the fall of the SDX/EN pin voltage, the IC becomes disable status when the voltage becomes  $V_{EN2}$  or less.

Shown as Figure 33, the SDX/EN pin realizes the enable control with the VIN pin by connecting the circuit divided by the resistor  $R_1$  and  $R_2$  between the VIN and AGND pins to the SDX/EN pin.

The internal clamp element turned on and the SDX/EN pin inflow current increases if the SDX/EN pin voltage becomes  $V_{CLPEN}$  or more.

6.1 Enable Voltage

It is possible to set the enable voltage at the rise of the VIN pin voltage  $V_{IN\_ENABLE}$  by the formula below.

$$V_{IN\_ENABLE} = V_{EN1} \times \frac{R_1 \times (R_2 + R_{SDX/EN1}) + R_2 \times R_{SDX/EN1}}{R_2 \times R_{SDX/EN1}} \quad [V]$$

where:

$V_{IN\_ENABLE}$  is the enable voltage at the rise of the VIN pin voltage.

$V_{EN1}$  is the enable voltage 1.

It is necessary to set the duty to  $D_{MAX}$  or less and operate in this IC's control method. Thus, set the enable voltage at the rise of the VIN pin voltage  $V_{IN\_ENABLE}$  to meet the conditional expression below.

$$V_{IN\_ENABLE} > \frac{N_P}{N_S} \times (V_{OUT} + V_F) \quad [V]$$

where:

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$V_{OUT}$  is the output voltage.

$V_F$  is the forward voltage at the secondary output diode.

6.2 Disable Voltage

It is possible to set the disable voltage at the fall of the VIN pin voltage  $V_{IN\_DISABLE}$  by the formula below.

$$V_{IN\_DISABLE} = V_{EN2} \times \frac{R_1 \times (R_2 + R_{SDX/EN1} + R_{SDX/EN2}) + R_2 \times (R_{SDX/EN1} + R_{SDX/EN2})}{R_2 \times (R_{SDX/EN1} + R_{SDX/EN2})} \quad [V]$$

$V_{IN\_DISABLE}$  is the disable voltage at the fall of the VIN pin voltage.

$V_{EN2}$  is the enable voltage 2.

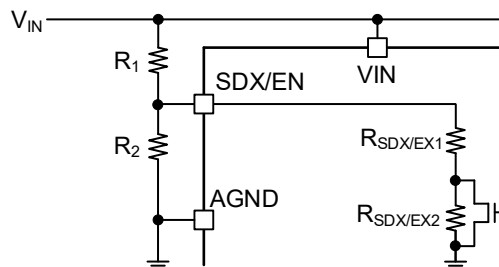


Figure 33. Position of Resistors Connected to SDX/EN Pin

Application Examples – continued

7 Enable OVP Detect Voltage and Enable OVP Release Voltage

This IC becomes disable status when the SDX/EN pin voltage becomes  $V_{ENOV1}$  or more. Also, the IC becomes enable status and starts the operation when the SDX/EN pin voltage becomes  $V_{ENOV2}$  or less.

Shown as Figure 34, the SDX/EN pin realizes the enable OVP control with the VIN pin by connecting the circuit divided by the resistor  $R_1$  and  $R_2$  between the VIN and AGND pins to the SDX/EN pin.

7.1 Enable OVP Detect Voltage

It is possible to set the enable OVP detect voltage of the VIN pin voltage  $V_{IN\_ENOV1}$  by the formula below.

$$V_{IN\_ENOV1} = V_{ENOV1} \times \frac{R_1 \times (R_2 + R_{SDX/EN3}) + R_2 \times R_{SDX/EN3}}{R_2 \times R_{SDX/EN3}} \quad [V]$$

where:

$V_{IN\_ENOV1}$  is the enable OVP detect voltage of the VIN pin voltage.

$V_{ENOV1}$  is the enable over protection voltage 1.

7.2 Enable OVP Release Voltage

It is possible to set the enable OVP release voltage of the VIN pin voltage  $V_{IN\_ENOV2}$  by the formula below.

$$V_{IN\_ENOV2} = V_{ENOV2} \times \frac{R_1 \times (R_2 + R_{SDX/EN3} + R_{SDX/EN4}) + R_2 \times (R_{SDX/EN3} + R_{SDX/EN4})}{R_2 \times (R_{SDX/EN3} + R_{SDX/EN4})} \quad [V]$$

$V_{IN\_ENOV2}$  is the enable OVP release voltage of the VIN pin voltage.

$V_{ENOV2}$  is the enable over protection voltage 2.

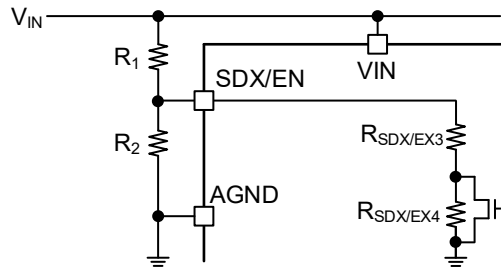


Figure 34. Position of Resistors Connected to SDX/EN Pin (EN OVP)





Application Examples – continued

9 The Influence to Switching Frequency and Output Voltage for Each Load

This IC achieves high efficiency by lowering the switching frequency in the light load. In CCM (Continuous Conduction Mode) operation, the switching frequency is  $f_{SW}$  for the constant load. When the load is light, the operation is changed from CCM to DCM (Discontinuous Conduction Mode). Then, the switching frequency is reduced from  $f_{SW}$ . The output load when the operation is changed from CCM to DCM  $I_{OUT\_f_{SW}1}$  is calculated by the formula below.

$$I_{OUT\_f_{SW}1} = \frac{1}{2} \times \frac{(V_{IN} \times Duty)^2}{L_P \times f_{SW} \times V_{OUT}} \times \eta$$

where:

$I_{OUT\_f_{SW}1}$  is the switched output current from CCM to DCM.

$f_{SW}$  is the switching frequency.

$V_{IN}$  is the VIN pin voltage.

$L_P$  is the primary side inductance.

$V_{OUT}$  is the output voltage.

$\eta$  is the efficiency.

As the load is lighter than  $I_{OUT\_f_{SW}1}$ , the on time decreases and becomes the minimum on time  $t_{ON\_MIN}$ . The load current when the on time becomes minimum on time  $I_{OUT\_f_{SW}2}$  is calculated by the formula below.

$$I_{OUT\_f_{SW}2} = \frac{1}{2} \times \frac{f_{SW} \times (V_{IN} \times t_{ON\_MIN})^2}{L_P \times V_{OUT}} \times \eta$$

where:

$I_{OUT\_f_{SW}2}$  is the load current operated by minimum on time.

$t_{ON\_MIN}$  is the minimum on time.

As the load is lighter than  $I_{OUT\_f_{SW}2}$ , the off time increases and becomes the maximum off time  $t_{OFF\_MAX}$ . Because the maximum off time  $t_{OFF\_MAX}$  is determined in this IC, the switching frequency is not smaller than the minimum switching frequency  $f_{SW\_MIN}$  calculated by the formula below.

$$f_{SW\_MIN} = \frac{1}{t_{ON\_MIN} + t_{OFF\_MAX}}$$

where:

$f_{SW\_MIN}$  is the minimum switching frequency.

$t_{OFF\_MAX}$  is the maximum off time.

Therefore, a certain amount of output power is absolutely generated by the minimum switching frequency operation. This is the reason for which the output voltage rises in the no load or the light load.

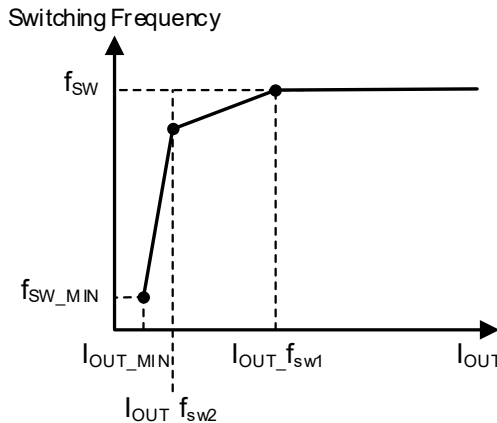


Figure 36. Switching Frequency vs I<sub>OUT</sub>

Application Examples – continued

10 Load Compensation Function

The load regulation of the output voltage is worsened by the forward voltage at the secondary output diode  $V_F$  and the secondary total impedance ESR. It becomes possible to improve the load regulation of the output voltage by using the load compensation function.

Incidentally, short the L\_COMP pin to the GND to invalidate this function.

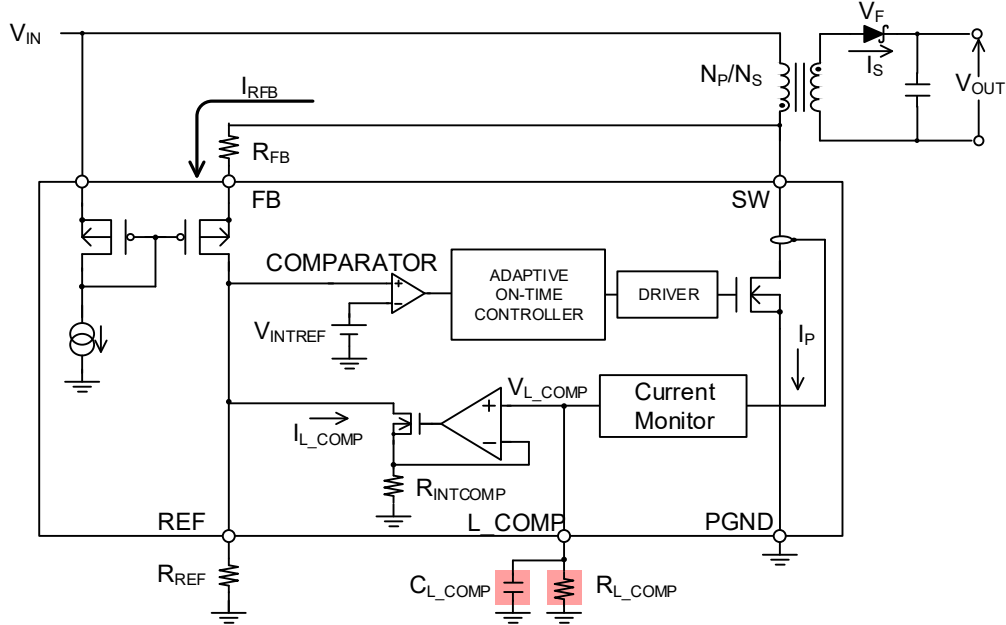


Figure 37. Block Diagram of Load Compensation

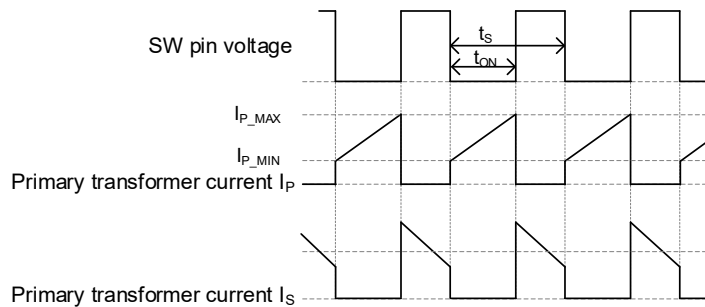


Figure 38. Switching Operation of Continuous Mode

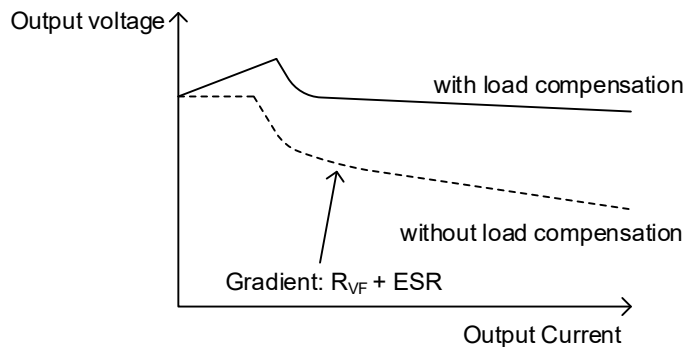


Figure 39. Image of Load Compensation

## 10 Load Compensation Function – continued

### 10.1 Setting of Amount of Load Compensation

This function compensates the drop of output voltage  $V_{OUT}$  corresponding to the average current of primary transformer current  $I_P$ .

The amount of load compensation is adjusted by the external capacitor  $C_{L\_COMP}$  and external resistor  $R_{L\_COMP}$  at the L\_COMP pin.

The relational formula between the primary transformer current  $I_P$  and the secondary transformer current  $I_S$  is shown below.

$$I_P = \frac{N_P}{N_S} \times I_S \quad [A]$$

where:

$I_P$  is the primary transformer current.

$N_P$  is the number of winding at the primary transformer.

$N_S$  is the number of winding at the secondary transformer.

$I_S$  is the secondary transformer current.

#### 10.1.1 Setting of External Resistor at L\_COMP Pin $R_{L\_COMP}$

It is necessary to calculate the L\_COMP pin current  $I_{L\_COMP}$  following the formula below for the setting of the external resistor at the L\_COMP pin  $R_{L\_COMP}$ .

$$I_{L\_COMP} = \frac{V_{L\_COMP}}{R_{INTCOMP}} \quad [A]$$

where:

$I_{L\_COMP}$  is the L\_COMP pin current.

$V_{L\_COMP}$  is the L\_COMP pin voltage.

$R_{INTCOMP}$  is the internal resistor at the L\_COMP pin.

L\_COMP pin voltage  $V_{L\_COMP}$  mentioned in the formula above is the value which is converted the current calculated by  $K \times I_P$  flowing from Current Monitor Block to the L\_COMP pin by the external resistor at the L\_COMP pin  $R_{L\_COMP}$ .

L\_COMP pin voltage  $V_{L\_COMP}$  is converted to L\_COMP pin current  $I_{L\_COMP}$  by the internal resistor at L\_COMP pin  $R_{INTCOMP}$ , and it compensates the REF pin current.

It is necessary to meet  $V_{L\_COMP} \leq 0.5$  V because the operational voltage's upper limit of  $V_{L\_COMP}$  is restricted by the internal circuit.

In addition, Connect the external capacitor at the L\_COMP pin  $C_{L\_COMP}$  because the rapid fluctuation of  $I_{L\_COMP}$  may make the  $V_{L\_COMP}$  unstable. The reference value of  $C_{L\_COMP}$  is 0.1  $\mu$ F.

From the above, it is necessary that  $V_{L\_COMP}$  meet the conditional expression below.

$$\begin{aligned} V_{L\_COMP} &= K \times R_{L\_COMP} \times I_{P\_AVE} \leq 0.5 \\ &= K \times R_{L\_COMP} \times \frac{I_{P\_MIN} + I_{P\_MAX}}{2} \times \frac{t_{ON}}{t_S} \leq 0.5 \quad [V] \end{aligned}$$

where:

$K$  is the compressor magnification in Current Monitor Block.

$R_{L\_COMP}$  is the external resistor at the L\_COMP pin.

$I_{P\_AVE}$  is the average value of primary transformer current  $I_P$ .

$I_{P\_MIN}$  is the minimum value of primary transformer current  $I_P$ .

$I_{P\_MAX}$  is the maximum value of primary transformer current  $I_P$ .

$t_S$  is the switching cycle.

$t_{ON}$  is the on time.

**10.1.1 Setting of External Resistor at L\_COMP Pin  $R_{L\_COMP}$  – continued**

By the load compensation function, the feedback current flowing at the external resistor between the REF and AGND pins  $R_{REF}$  is reduced by  $I_{L\_COMP}$  from its original current value. As the result, the primary flyback voltage rises and the dropped output voltage  $V_{OUT}$  is compensated.

The output voltage  $V_{OUT}$  when the load compensation function operates is calculated by the formula below.

$$V_{OUT} = \frac{N_S}{N_P} \times \left( \frac{V_{REF}}{R_{REF}} + I_{L\_COMP} \right) \times R_{FB} - V_F - I_{S\_AVE} \times ESR \quad [V]$$

where:

$V_{OUT}$  is the output voltage.

$N_S$  is the number of winding at the secondary transformer.

$N_P$  is the number of winding at the primary transformer.

$V_{REF}$  is the REF pin voltage.

$R_{REF}$  is the external resistor between the REF and AGND pins.

$I_{L\_COMP}$  is the L\_COMP pin current.

$R_{FB}$  is the external resistor between the FB and SW pins.

$V_F$  is the forward voltage at the secondary output diode.

$I_{S\_AVE}$  is the average value of the secondary transformer current  $I_s$ .

$ESR$  is the secondary total impedance (secondary transformer winding resistance and board).

Reference: The output voltage  $V_{OUT}$  at normal operation

$$V_{OUT} = \frac{N_S}{N_P} \times \frac{R_{FB}}{R_{REF}} \times V_{REF} - V_F - I_{S\_AVE} \times ESR \quad [V]$$

According to the formula above, it is necessary to establish the next formula to remove the forward voltage at the secondary output diode  $V_F$  and the secondary total impedance  $ESR$  by the load compensation function.

$$I_{L\_COMP} \times \frac{N_S}{N_P} \times R_{FB} = V_F + I_{S\_AVE} \times ESR$$

Next, calculate the  $R_{L\_COMP}$  by making the linear approximation  $R_{VF}$  of the fluctuation of the forward voltage at the secondary output diode  $V_F$  corresponding to the secondary transformer current  $I_s$ .

$$\frac{K \times R_{L\_COMP} \times I_{P\_AVE}}{R_{INTCOMP}} \times \frac{N_S}{N_P} \times R_{FB} = I_{S\_AVE} \times R_{VF} + I_{S\_AVE} \times ESR$$

$$\frac{K \times R_{L\_COMP}}{R_{INTCOMP}} \times \left( \frac{N_S}{N_P} \right)^2 \times R_{FB} = (R_{VF} + ESR)$$

From the above,

$$R_{L\_COMP} = R_{INTCOMP} \times \frac{R_{VF} + ESR}{K \times R_{FB}} \times \left( \frac{N_P}{N_S} \right)^2 \quad [\Omega]$$

where:

$K$  is the compressor magnification in Current Monitor Block.

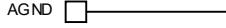
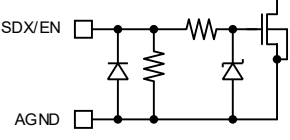
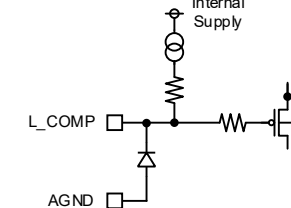
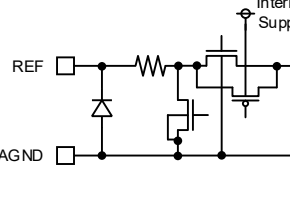
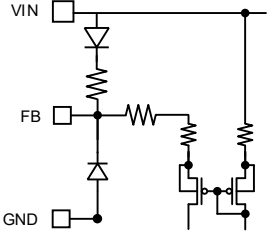
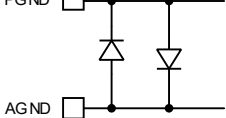
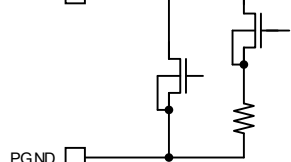
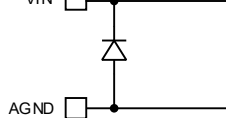
$R_{L\_COMP}$  is the external resistor at the L\_COMP pin.

$I_{P\_AVE}$  is the average value of primary transformer current  $I_P$ .

$R_{INTCOMP}$  is the internal resistor at the L\_COMP pin.

The values of  $R_{VF}$  and  $ESR$  depend on the operating environment such as use parts and mounting boards. When setting the  $R_{L\_COMP}$ , adjust it monitoring the output voltage  $V_{OUT}$  in the range of using load current certainly.

I/O Equivalence Circuit

<p>1</p> <p>AGND</p> 	<p>2</p> <p>SDX/EN</p> 	<p>3</p> <p>L_COMP</p> 	<p>4</p> <p>REF</p> 
<p>5</p> <p>FB</p> 	<p>6</p> <p>PGND</p> 	<p>7</p> <p>SW</p> 	<p>8</p> <p>VIN</p> 

## Operational Notes

### 1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

### 2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

### 3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

### 4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

### 5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

### 6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

### 7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

### 8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

### 9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

## Operational Notes – continued

**10. Regarding the Input Pin of the IC**

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When  $GND > Pin A$  and  $GND > Pin B$ , the P-N junction operates as a parasitic diode.

When  $GND > Pin B$ , the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

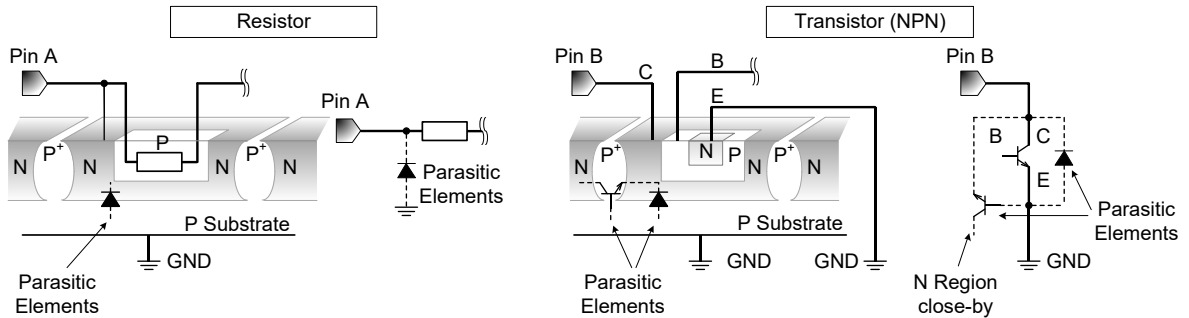


Figure 40. Example of Monolithic IC Structure

**11. Ceramic Capacitor**

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

**12. Thermal Shutdown Circuit (TSD)**

This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature ( $T_j$ ) will rise which will activate the TSD circuit that will turn OFF power output pins. When the  $T_j$  falls below the TSD threshold, the circuits are automatically restored to normal operation.

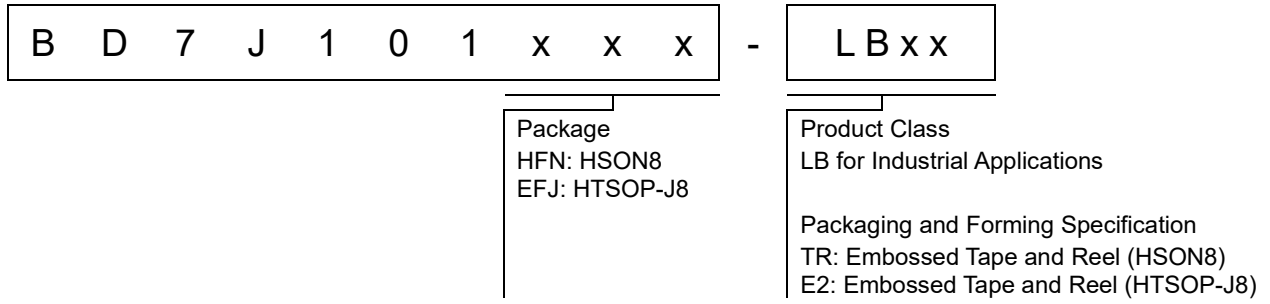
Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

**13. Over Current Protection Circuit (OCP)**

This IC incorporates an integrated over current protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.



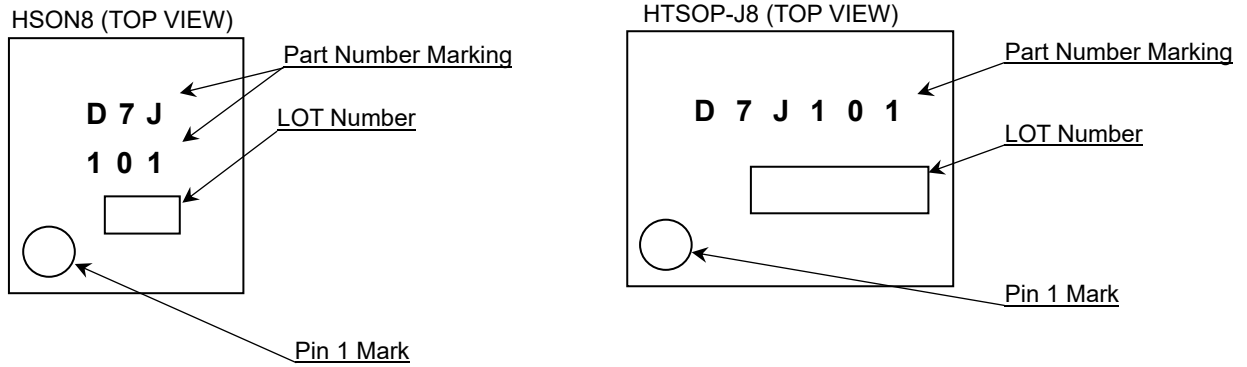
Ordering Information



Lineup

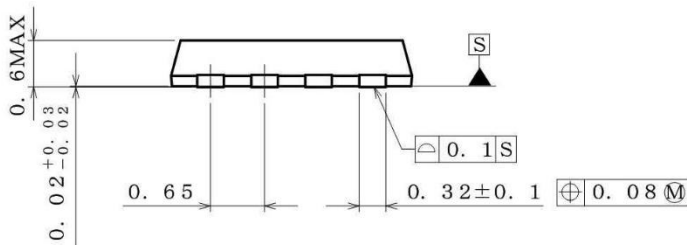
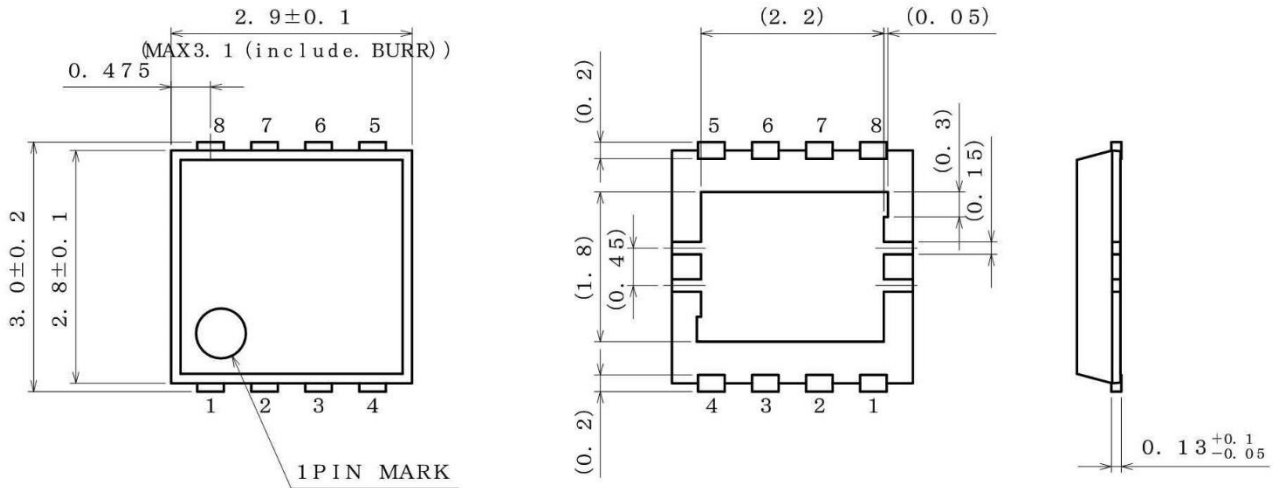
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BD7J101HFN-LB (Under Development)	D7J101	BD7J101HFN-LBTR	HSON8
BD7J101EFJ-LB	D7J101	BD7J101EFJ-LBE2	HTSOP-J8

Marking Diagrams



Physical Dimension and Packing Information

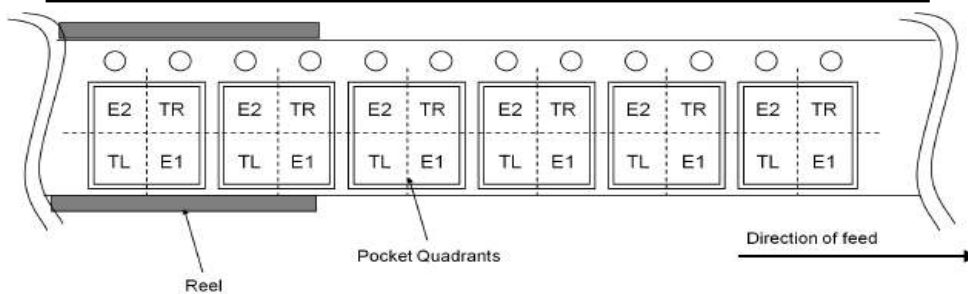
Package Name	HSON8
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(UNIT : mm)  
 PKG : HSON8  
 Drawing No. EX163-5002

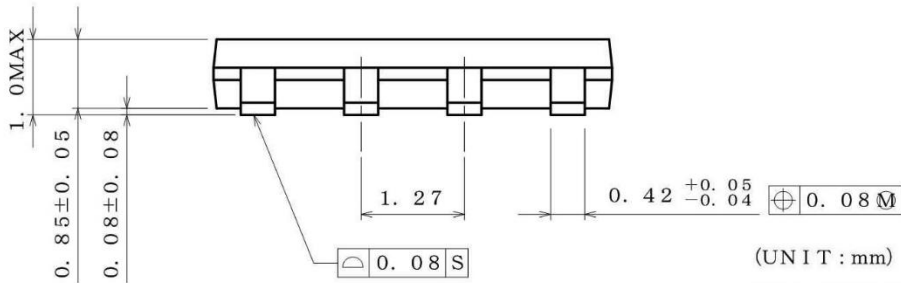
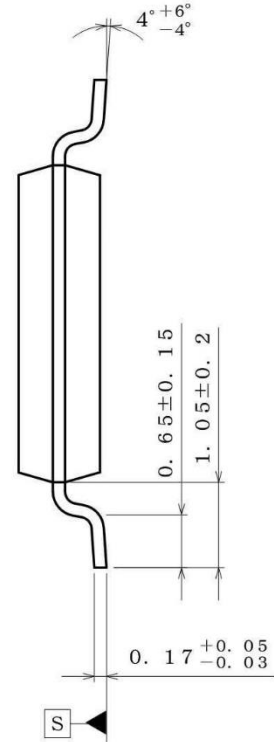
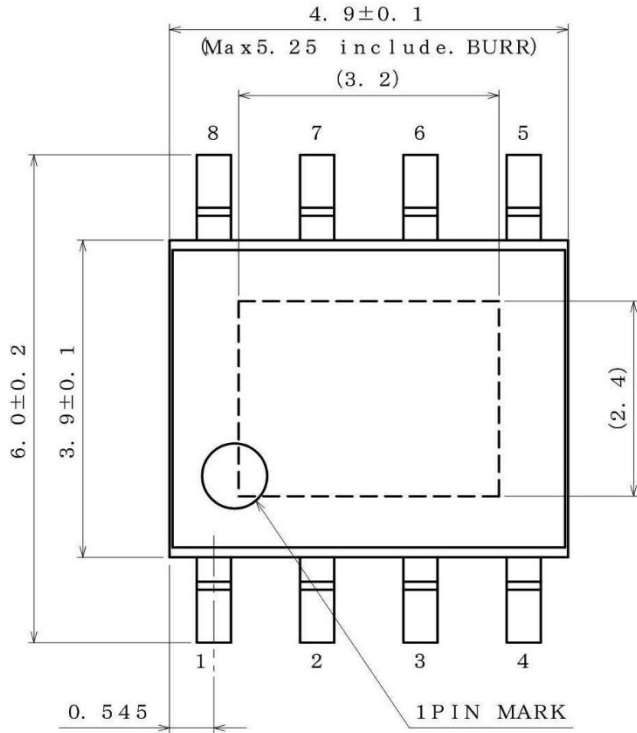
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Quantity	3000pcs
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Physical Dimension and Packing Information – continued

Package Name	HTSOP-J8
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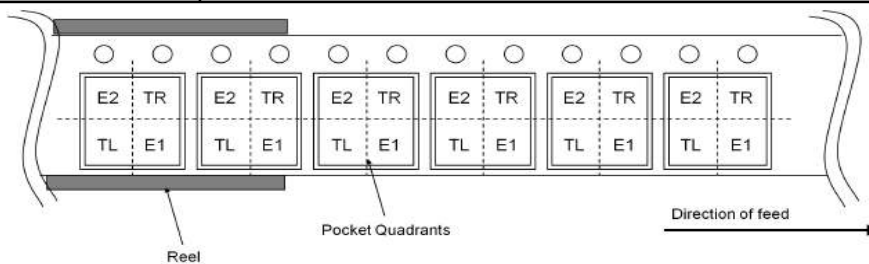
(UNIT : mm)

PKG : HTSOP-J8

Drawing No. EX169-5002-2

< Tape and Reel Information >

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Quantity	2500pcs
Direction of feed	E2 The direction is the pin 1 of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand



**Revision History**

Date	Revision	Changes
14.Sep.2021	001	New Release

# Notice

## Precaution on using ROHM Products

1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment <sup>(Note 1)</sup>, aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASS III	CLASS III	CLASS II b	CLASS III
CLASS IV		CLASS III	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
  - [a] Installation of protection circuits or other protective devices to improve system safety
  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc. prior to use, must be necessary:
  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
4. The Products are not subject to radiation-proof design.
5. Please verify and confirm characteristics of the final or mounted products in using the Products.
6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
8. Confirm that operation temperature is within the specified range described in the product specification.
9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

## Precaution for Mounting / Circuit board design

1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

### Precautions Regarding Application Examples and External Circuits

1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

### Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of ionizer, friction prevention and temperature / humidity control).

### Precaution for Storage / Transportation

1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

### Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

### Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

### Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

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